

DATA SHEET

2PD602; 2PD602A NPN general purpose transistors

Product specification
Supersedes data of October 1993
File under Discrete Semiconductors, SC04

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Philips Semiconductors



PHILIPS

NPN general purpose transistors

2PD602; 2PD602A

FEATURES

- Large collector current
- Low collector-emitter saturation voltage
- S-mini package.

APPLICATIONS

Intended for general purpose switching or amplification.

DESCRIPTION

NPN transistor in a plastic SC59 package. Complementary pairs are 2PB710 and 2PB710A respectively.

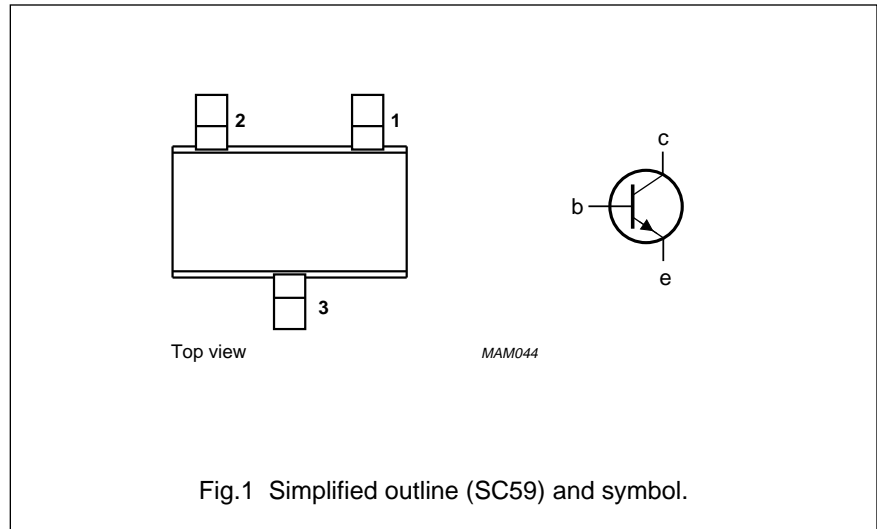


Fig.1 Simplified outline (SC59) and symbol.

MARKING

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| 2PD602Q | WQ |
| 2PD602R | WR |
| 2PD602S | WS |
| 2PD602AQ | XQ |
| 2PD602AR | XR |
| 2PD602AS | XS |

PINNING SC59

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2 | emitter |
| 3 | collector |

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|---------------------------|--|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | | | |
| | 2PD602 | | – | 30 | V |
| | 2PD602A | | – | 60 | V |
| V_{CEO} | collector-emitter voltage | open base | | | |
| | 2PD602 | | – | 25 | V |
| | 2PD602A | | – | 50 | V |
| I_{CM} | peak collector current | | – | 1 | A |
| P_{tot} | total power dissipation | up to $T_{amb} = 25\text{ °C}$ | – | 250 | mW |
| h_{FE} | DC current gain | $I_C = 150\text{ mA};$ $V_{CE} = 10\text{ V}$ | 85 | 340 | |
| f_T | transition frequency | $I_E = -50\text{ mA};$ $V_{CB} = 10\text{ V}$ | | | |
| | 2PD602S | | 180 | – | MHz |
| | 2PD602AS | | 180 | – | MHz |

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|-------------------------------|---|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | | | |
| | 2PD602 | | – | 30 | V |
| | 2PD602A | | – | 60 | V |
| V_{CEO} | collector-emitter voltage | open base | | | |
| | 2PD602 | | – | 25 | V |
| | 2PD602A | | – | 50 | V |
| V_{EBO} | emitter-base voltage | open collector | – | 5 | V |
| I_C | collector current (DC) | | – | 500 | mA |
| I_{CM} | peak collector current | | – | 1 | A |
| P_{tot} | total power dissipation | up to $T_{amb} = 25\text{ °C}$; note 1 | – | 250 | mW |
| T_{stg} | storage temperature | | –65 | +150 | °C |
| T_j | junction temperature | | – | 150 | °C |
| T_{amb} | operating ambient temperature | | –65 | +150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------|---|---------------------|-------|------|
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | in free air; note 1 | 500 | K/W |

Note to the “Limiting values” and “Thermal characteristics”

1. Refer to SC59 standard mounting conditions.

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2PD602; 2PD602A

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|---------------|---|---|------|------|---------------|
| $V_{(BR)CBO}$ | collector-base breakdown voltage 2PD602 2PD602A | open emitter; $I_C = 10\text{ }\mu\text{A}$; $I_E = 0$ | 30 | – | V |
| | | | 60 | – | V |
| $V_{(BR)CEO}$ | collector-emitter breakdown voltage 2PD602 2PD602A | open base; $I_C = 2\text{ mA}$; $I_B = 0$; note 1 | 25 | – | V |
| | | | 50 | – | V |
| $V_{(BR)EBO}$ | emitter-base breakdown voltage | open collector; $I_E = -10\text{ }\mu\text{A}$; $I_C = 0$ | 5 | – | V |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 300\text{ mA}$; $I_B = 30\text{ mA}$; note 1 | – | 600 | mV |
| I_{CBO} | collector cut-off current | $V_{CB} = 20\text{ V}$; $I_E = 0$ | – | 100 | nA |
| | | $V_{CB} = 20\text{ V}$; $I_E = 0$; $T_j = 150\text{ °C}$ | – | 5 | μA |
| I_{EBO} | emitter cut-off current | $V_{EB} = 4\text{ V}$; $I_C = 0$ | – | 100 | nA |
| h_{FE} | DC current gain | $V_{CE} = 10\text{ V}$; $I_C = 500\text{ mA}$; note 1 | 40 | – | |
| h_{FE} | DC current gain 2PD602Q; 2PD602AQ 2PD602R; 2PD602AR 2PD602S; 2PD602AS | $V_{CE} = 10\text{ V}$; $I_C = 150\text{ mA}$; note 1 | 85 | 170 | |
| | | | 120 | 240 | |
| | | | 170 | 340 | |
| f_T | transition frequency 2PD602Q; 2PD602AQ 2PD602R; 2PD602AR 2PD602S; 2PD602AS | $V_{CB} = 10\text{ V}$; $I_E = -50\text{ mA}$; $f = 100\text{ MHz}$; note 1 | 140 | – | MHz |
| | | | 160 | – | MHz |
| | | | 180 | – | MHz |
| C_c | collector capacitance | $V_{CB} = 10\text{ V}$; $I_E = I_C = 0$; $f = 1\text{ MHz}$ | – | 15 | pF |

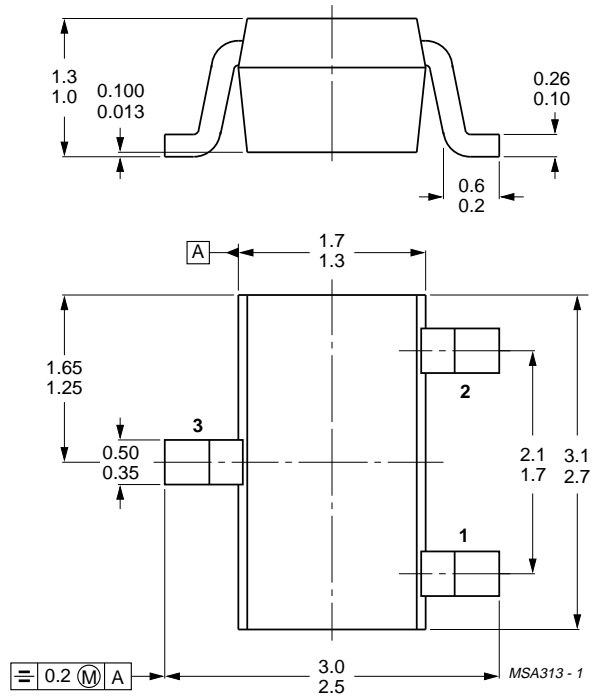
Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

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PACKAGE OUTLINE



Dimensions in mm.

Fig.2 SC59.

NPN general purpose transistors

2PD602; 2PD602A

DEFINITIONS

| | |
|---|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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